

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,936,897 B2
APPLICATION NO. : 09/259145
DATED : August 30, 2005
INVENTOR(S) : Pai-Hung Pan and Nanseng Jeng

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the title page:

In Item (54) TITLE

change "INTERMEDIATE STRUCTURE
HAVING A SILICON BARRIER LAYER
ENCAPSULATING A SEMICONDUCTOR
SUBSTRATE" to --INTERMEDIATE
STRUCTURE HAVING A SILICON
NITRIDE BARRIER LAYER
ENCAPSULATING A SEMICONDUCTOR
SUBSTRATE--

In ITEM (57) ABSTRACT, 12th line,

change "unmasked potion" to --unmasked
portions--

In the specification:

COLUMN 1, LINE 2,

change "SILICON BARRIER LAYER" to
--SILICON NITRIDE BARRIER--

COLUMN 1, LINE 38,

change "layer 210 maybe" to --layer 210 may
be--

COLUMN 2, LINE 24,

change "(see U.S. Pat." to --(see U.S. Pat.--

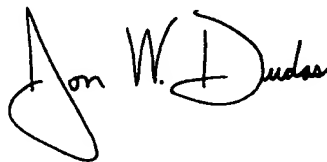
In the claims:

CLAIM 9, COLUMN 7, LINE 28,

change "first substrate" to --first surface--

Signed and Sealed this

Eighteenth Day of December, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office